



COPY OF PAPER
ORIGINALLY FILED

- 1 -

Docket No. 0756-2330

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#12/c
9/19/02
Jum

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/894,125

Filed: June 29, 2001

For: CRYSTALLINE SEMICONDUCTOR)

THIN FILM, METHOD OF FABRICATING)

THE SAME, SEMICONDUCTOR DEVICE,))

AND METHOD OF FABRICATING THE)

SAME)

) Art Unit: 2823

) Examiner: B. Kebede

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
The United States Postal Service with sufficient postage as First
Class Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on 9/26/02

Ava M. Dixon

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated April 24, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-6, 10-12 and 19-30 as follows:

RECEIVED
SEP 12 2002
TECHNOLOGY CENTER-2800

- DI SUB
- C1
1. (Amended) A method of manufacturing a semiconductor device comprising the steps of
forming a semiconductor film comprising silicon over a substrate;
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;
removing an oxide film formed on a surface of the semiconductor film by etching after the irradiation of the laser light; and
leveling the surface of the semiconductor film by heating after removing said oxide film.